

AMENDMENT UNDER 37 C.F.R. 1.111  
U.S. Appln. No. 10/009,796  
Attorney Docket No. Q67530

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

- 1-28. (canceled).
29. (new): A semiconductor production apparatus comprising a sealing material obtained by crosslinking and molding a crosslinkable elastomer composition comprising a crosslinkable fluorine-containing elastomer component and ultra fine powders of silicon oxide; said ultra fine powders of silicon oxide having dioctylphthalate adsorption of not more than 8  $\mu\text{g}$  per 1 g of silicon oxide and an average particle size of not more than 0.5  $\mu\text{m}$ , said sealing material generating dioctylphthalate gas when heated at 200°C for 15 minutes in an amount of not more than 1 ppb, and said semiconductor production apparatus being an etching system, a cleaning system, an exposing system, a polishing system, a film forming system or a diffusion and ion implantation system.
30. (new): The semiconductor production apparatus of Claim 29, wherein the ultra fine powders of silicon oxide have  $100 \times 10^{19}$  or less hydroxyl groups per gram on surfaces thereof.

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31. (new): The semiconductor production apparatus of Claim 29, wherein an average particle size of the ultra fine powders of silicon oxide is from 0.01 to 0.05  $\mu\text{m}$ .

32. (new): The semiconductor production apparatus of Claim 29, wherein the ultra fine powders of silicon oxide are an amorphous silica.

33. (new): The semiconductor production apparatus of Claim 29, wherein the ultra fine powders of silicon oxide are surface-treated with hydrofluoric acid.

34. (new): The semiconductor production apparatus of Claim 29, wherein the ultra fine powders of silicon oxide are surface-treated with a silane coupling agent.

35. (new): The semiconductor production apparatus of Claim 29, wherein the ultra fine powders of silicon oxide are heat-treated at a high temperature of not less than 400°C in an inert gas stream.

36. (new): The semiconductor production apparatus of Claim 29 which comprises 1 to 150 parts by weight of said ultra fine powders of silicon oxide on the basis of 100 parts by weight of the crosslinkable elastomer component.

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37. (new): The semiconductor production apparatus of Claim 29 which comprises 0.05 to 10 parts by weight of an organic peroxide, 0.1 to 10 parts by weight of a crosslinking aid and 1 to 150 parts by weight of said ultra fine powders of silicon oxide on the basis of 100 parts by weight of the crosslinkable elastomer component.

38. (new): The semiconductor production apparatus of Claim 29, wherein the fluorine-containing elastomer is a perfluoro elastomer.